Abstracts

Low-frequency noise figures-of-merit in RF SiGe HBT technology (2002 Vol. I [MWSYM])

Jin Tang, Guofu Niu, Zhenrong Jin, J.D. Cressler, Shiming Zhang, A.J. Joseph and D.L. Harame. "Low-frequency noise figures-of-merit in RF SiGe HBT technology (2002 Vol. I [MWSYM])." 2002 MTT-S International Microwave Symposium Digest 02.1 (2002 Vol. I [MWSYM]): 179-182 vol.1.

We present the first systematic experimental and modeling results of corner frequency (f/sub C/) and the corner frequency to cut-off frequency ratio (f/sub C//f/sub T/) for SiGe HBTs in a commercial SiGe RF technology. The f/sub C//f/sub T/ ratio is examined as a function of biasing current for SiGe HBTs featuring multiple collector doping profiles (breakdown voltages) and multiple SiGe profiles.

❑ Return to main document.